# 100 mA, 5.0 V, Low Dropout Voltage Regulator with Reset and Sense

The NCV4949C is a monolithic integrated 5.0 V voltage regulator with a very low dropout and additional functions such as reset and an uncommitted voltage sense comparator.

It is designed for supplying microcontroller/microprocessor controlled systems particularly in automotive applications. The NCV4949C has improved reset behavior for lower input and output voltage levels.

#### **Features**

- Operating DC Supply Voltage Range 5.5 V to 40 V
- High Precision Output Voltage 5.0 V ±1%
- Output Current Capability Up to 100 mA
- Very Low Dropout Voltage Less Than 0.4 V
- Reset Circuit Sensing The Output Voltage
- Programmable Reset Pulse Delay
- Voltage Sense Comparator
- Fault Protection, +60 V Peak Transient Voltage, -40 V Reverse Voltage, Short Circuit, Thermal Overload
- NCV Prefix for Automotive and Other Applications Requiring Site and Change Control
- These are Pb-Free Devices

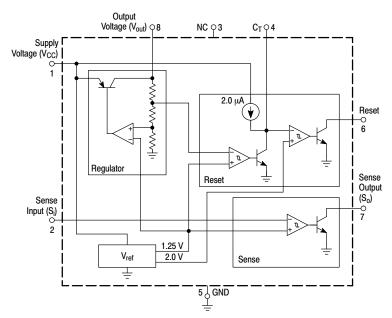


Figure 1. Representative Block Diagram

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SOIC-8 D SUFFIX CASE 751-07





SOIC-8 EP PD SUFFIX CASE 751AC



A = Assembly Location

= Wafer Lot

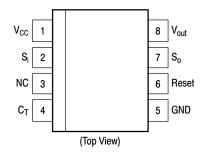
/ = Year

W = Work Week

= Pb-Free Device

(Note: Microdot may be in either location)

#### **PIN CONNECTIONS**



#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

#### **PIN FUNCTION DESCRIPTION**

SO-8 Pin#	SO-8 EP	Symbol	Description	
1	1	V <sub>CC</sub>	Supply Voltage	
2	2	S <sub>i</sub>	Input of Sense Comparator	
4	4	C <sub>T</sub>	Reset Delay Capacitor	
5	5	GND	Ground	
6	6	Reset	Output of Reset Comparator	
7	7	S <sub>O</sub>	Output of Sense Comparator	
8	8	V <sub>out</sub>	Main Regulator Output	
3	3	NC	No Connect	
-	EPAD	EPAD	Connect to Ground potential or leave unconnected	

#### **MAXIMUM RATINGS**

Rating		Symbol	Min	Max	Unit
DC Operating Supply Voltage		$V_{CC}$	5.5	40	V
Input to Regulator		$V_{CC}$	-40	45	V
Transient Supply Voltage (Note 1)		V <sub>CC TR</sub>	-	60	V
Output		V <sub>out</sub> I <sub>out</sub>	-0.5 -10	20 Internally Limited	V mA
Sense Input		V <sub>SI</sub> I <sub>SI</sub>	-40 -1.0	45 1.0	V mA
Sense Output		V <sub>SO</sub> I <sub>SO</sub>	-0.3 -5.0	7.0 5.0	V mA
Reset Output		V <sub>Reset</sub> I <sub>Reset</sub>	-0.3 -5.0	7.0 5.0	V mA
Reset Delay		V <sub>CT</sub> I <sub>CT</sub>	-0.3 Internally Limited	7.0 Internally Limited	V mA
ESD Protection at any pin	Human Body Model Machine Model	-	- -	4000 400	V
Operating Junction Temperature Range		TJ	-40	+150	°C
Storage Temperature Range		T <sub>STG</sub>	-50	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic		Test Conditions (Typical Values)			Unit
		Note 2	Note 3	Note 4	
SOIC-8	Junction-to-Lead ( $\Psi_{JLx6}$ $\theta_{JL6}$ ) Junction-to-Ambient ( $R_{\theta JA}$ , $\theta_{JA}$ )	65.6 169.4	62 147.6	61 127.2	°C/W
SOIC-8 EP	Junction-to-Lead ( $\Psi_{\text{JL6}},\theta_{\text{JL6}}$ ) Junction-to-Ambient ( $R_{\theta \text{JA}},\theta_{\text{JA}}$ )	36.1 109.2	32.1 91.1	27.4 71.9	°C/W

- 2. 1 oz. Copper, 100 mm sq. Copper area, 1.5 mm thick FR-4.
- 3. 1 oz. Copper, 200 mm sq. Copper area, 1.5 mm thick FR-4.
- 4. 1 oz. Copper, 500 mm sq. Copper area, 1.5 mm thick FR-4.

#### **LEAD TEMPERATURE SOLDERING REFLOW (Note 5)**

Rating	Symbol	Min	Max	Unit
Reflow (SMD styles only) lead free 60 - 150 sec above 217, 40 sec max at peak	pove 217, 40 sec max at peak Tsld – 260			°C
Moisture Sensitivity Level (SOIC-8)	MSL	Level 1		
Moisture Sensitivity Level (SOIC-8EP)	MSL	Level 2		

5. Per IPC / JEDEC J-STD-020C.

<sup>1.</sup> Load Dump Test B (with centralized load dump suppression) according to ISO16750-2 standard. Guaranteed by design. Not tested in production. Passed Class C according to ISO16750-1.

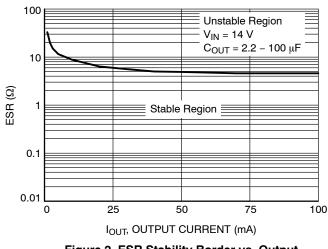
## $\textbf{ELECTRICAL CHARACTERISTICS} \ \ (V_{CC} = 14 \ V, \, -40^{\circ}C < T_{J} < 150^{\circ}C, \, unless \, otherwise \, specified.)$

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (T <sub>J</sub> = 25°C, I <sub>out</sub> = 1.0 mA)	V <sub>out</sub>	4.95	5.0	5.05	V
Output Voltage (6.0 V < V <sub>CC</sub> < 28 V, 1.0 mA < I <sub>out</sub> < 50 mA)	V <sub>out</sub>	4.9	5.0	5.1	V
Output Voltage (V <sub>CC</sub> = 35 V, t < 1.0 s, 1.0 mA < I <sub>out</sub> < 50 mA)	V <sub>out</sub>	4.9	5.0	5.1	V
Dropout Voltage	$V_{drop}$				V
I <sub>out</sub> = 10 mA		-	0.08	0.25	
I <sub>out</sub> = 50 mA		-	0.18	0.40	
I <sub>out</sub> = 100 mA		-	0.22	0.50	
Input to Output Voltage Difference in Undervoltage Condition	V <sub>IO</sub>	-	0.12	0.4	V
(V <sub>CC</sub> = 4.0 V, I <sub>out</sub> = 35 mA)					
Line Regulation (6.0 V < V <sub>CC</sub> < 28 V, I <sub>out</sub> = 1.0 mA)	Reg <sub>line</sub>	-	1.0	20	mV
Load Regulation (1.0 mA < I <sub>out</sub> < 100 mA)	Reg <sub>load</sub>	-	1.0	30	mV
Current Limit	I <sub>Lim</sub>				mA
V <sub>out</sub> = 4.5 V		105	320	400	
$V_{out} = 0 V$		_	220	_	
Quiescent Current (I <sub>out</sub> = 0.3 mA, T <sub>J</sub> < 100°C)	I <sub>QSE</sub>	-	120	260	μΑ
Quiescent Current (I <sub>out</sub> = 100 mA)	IQ	_	-	5.0	mA
RESET					
Reset Threshold Voltage	V <sub>Resth</sub>	-	4.5	-	V
Reset Threshold Hysteresis	V <sub>Resth,hys</sub>				mV
@ T <sub>J</sub> = 25°C		50	100	200	
@ $T_J = -40 \text{ to } +125^{\circ}\text{C}$		50	_	300	
Reset Pulse Delay (C <sub>T</sub> = 100 nF, t <sub>R</sub> ≥ 100 μs)	t <sub>ResD</sub>	55	100	180	ms
Reset Reaction Time (C <sub>T</sub> = 100 nF)	t <sub>ResR</sub>	-	5.0	30	μs
Reset Output Low Voltage (R <sub>Reset</sub> = 10 k $\Omega$ to V <sub>out</sub> , V <sub>CC</sub> $\geq$ 3.0 V)	V <sub>ResL</sub>	-	-	0.3	V
Reset Output High Leakage Current (V <sub>Reset</sub> = 5.0 V)	I <sub>ResH</sub>	-	-	1.0	μΑ
Delay Comparator Threshold	V <sub>CTth</sub>	-	2.0	-	V
Delay Comparator Threshold Hysteresis	V <sub>CTth, hys</sub>	-	100	-	mV
SENSE	•	<u>'</u>			
Sense Low Threshold (V <sub>SI</sub> Decreasing = 1.5 V to 1.0 V)	V <sub>SOth</sub>	1.16	1.25	1.35	V
Sense Threshold Hysteresis	V <sub>SOth,hys</sub>	20	100	200	mV
Sense Output Low Voltage (V <sub>SI</sub> $\leq$ 1.16 V, V <sub>CC</sub> $\geq$ 3.0 V, R <sub>SO</sub> = 10 k $\Omega$ to V <sub>out</sub> )	V <sub>SOL</sub>	-	-	0.4	V
Sense Output Leakage ( $V_{SO}$ = 5.0 V, $V_{SI}$ $\geq$ 1.5 V)	I <sub>SOH</sub>	-	-	1.0	μΑ
Sense Input Current	I <sub>SI</sub>	-1.0	0.1	1.0	μΑ
THERMAL SHUTDOWN		•		•	
Thermal Shutdown Temperature (I <sub>out</sub> = 1 mA) (Note 6)	T <sub>SD</sub>	150	_	200	°C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Values based on design and/or characterization.

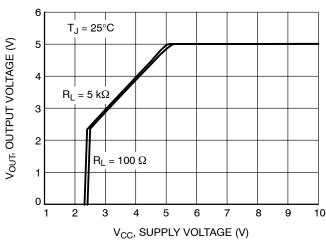
#### **TYPICAL CHARACTERISTICS**



5.04  $V_{CC} = 14 \text{ V}$ 5.03  $I_{OUT} = 1.0 \text{ mA}$ V<sub>OUT</sub>, OUTPUT VOLTAGE (V) 5.02 5.01 5.00 4.99 4.98 4.97 4.96 40 120 -40 80 160 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 2. ESR Stability Border vs. Output Current

Figure 3. Output Voltage vs. Junction Temperature



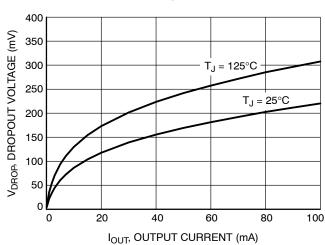
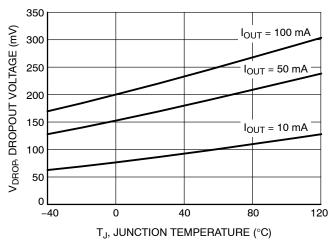


Figure 4. Output Voltage vs. Supply Voltage

Figure 5. Dropout Voltage vs. Output Current



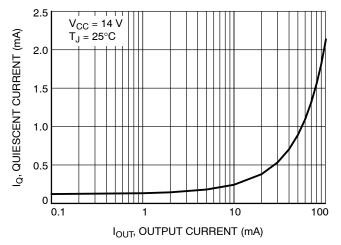


Figure 6. Dropout Voltage vs. Junction Temperature

Figure 7. Quiescent Current vs. Output Current

#### **TYPICAL CHARACTERISTICS**

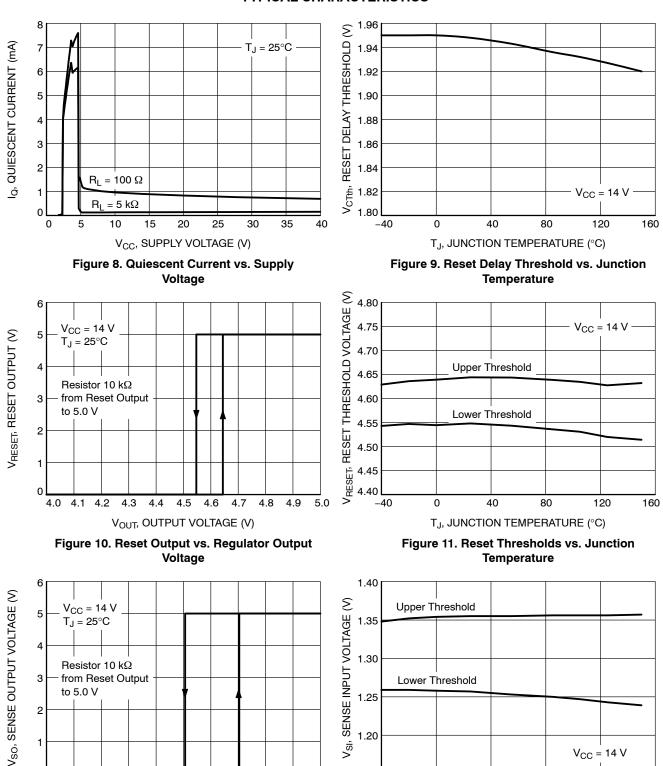


Figure 12. Sense Output vs. Sense Input Voltage

V<sub>SI</sub>, SENSE INPUT VOLTAGE (V)

1.3

1.2

1.0

Figure 13. Sense Thresholds vs. Junction Temperature

T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

80

120

160

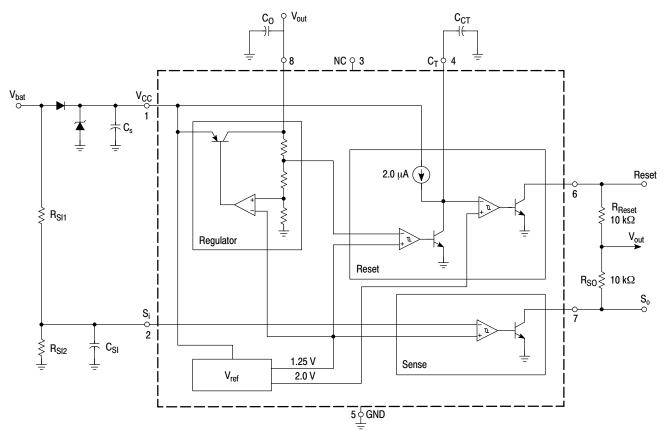
40

1.5

1.15

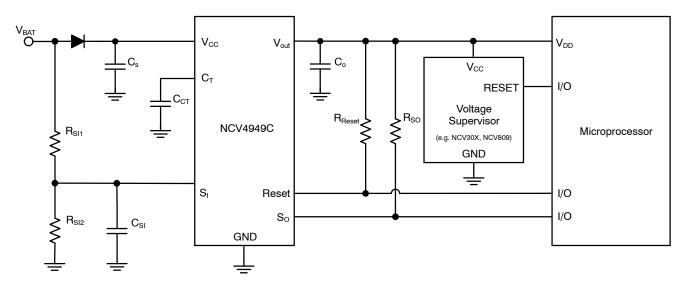
-40

#### **APPLICATION INFORMATION**



NOTE: 1. For good dynamic performance:  $C_s \ge 1.0~\mu\text{F},~C_O \ge 4.7~\mu\text{F},~ESR < 4.5~\Omega$  at 10 kHz

Figure 14. Application Schematic



NOTE: The NCV4949C is not developed in compliance with ISO26262 standard. If application is safety critical then the above application diagram shown in Figure 15 can be used.

Figure 15. Application Diagram

#### **OPERATING DESCRIPTION**

The NCV4949C is a monolithic integrated low dropout voltage regulator. Several outstanding features and auxiliary functions are implemented to meet the requirements of supplying microprocessor systems in automotive applications. It is also suitable in other applications where the included functions are required. The modular approach of this device allows the use of other features and functions independently when required.

#### Voltage Regulator

The voltage regulator uses a lateral PNP transistor as a regulating element. With this structure, very low dropout voltage at currents up to 100 mA is obtained. The dropout operation of the standby regulator is maintained typically down to 2.5 V input supply voltage.

A typical curve showing the standby output voltage as a function of the input supply voltage is shown in Figure 17.

The current consumption of the device (quiescent current) is less than 200  $\mu A$ .

To reduce the quiescent current peak in the undervoltage region and to improve the transient response in this region, the dropout voltage is controlled. The quiescent current as a function of the supply input voltage is shown in Figure 18.

#### Short Circuit Protection:

The maximum output current is internally limited. In case of short circuit, the output current is foldback current limited as described in Figure 16.

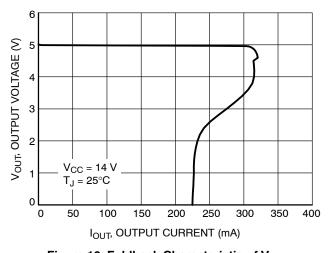


Figure 16. Foldback Characteristic of Vout

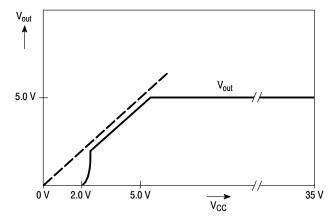


Figure 17. Output Voltage vs. Supply Voltage

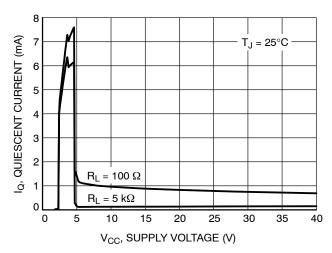


Figure 18. Quiescent Current vs. Supply Voltage

#### **Reset Circuit**

The block circuit diagram of the reset circuit is shown in Figure 19.

The reset circuit supervises the output voltage. The reset threshold of 4.5 V is defined by the internal reference voltage and standby output divider.

The reset pulse delay time  $t_{RD}$ , is defined by the charge time of an external capacitor  $C_T$ :

$$t_{RD} = \frac{C_T \times 2.0 \text{ V}}{2.0 \, \mu A}$$

The reaction time of the reset circuit originates from the discharge time limitation of the reset capacitor  $C_T$  and is proportional to the value of  $C_T$ . The reaction time of the reset circuit increases the noise immunity.

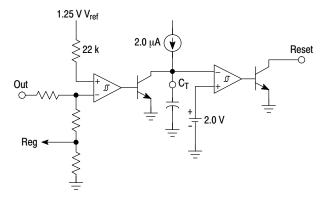


Figure 19. Reset Circuit

Output voltage drops below the reset threshold only marginally longer than the reaction time results in a shorter reset delay time.

The nominal reset delay time will be generated for output voltage drops longer than approximately 50 µs. The typical reset output waveforms are shown in Figure 20.

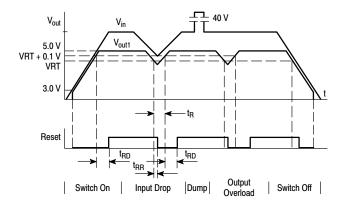


Figure 20. Typical Reset Output Waveforms

#### **Sense Comparator**

The sense comparator compares an input signal with an internal voltage reference of typical 1.25 V. The use of an external voltage divider makes this comparator very flexible in the application.

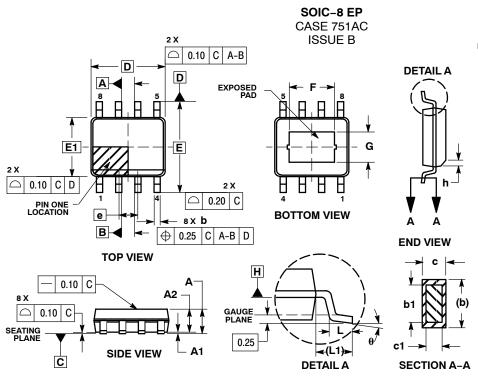
It can be used to supervise the input voltage either before or after a protection diode and to provide additional information to the microprocessor such as low voltage warnings.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NCV4949CDR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV4949CPDR2G	SOIC-8 EP (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications,including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

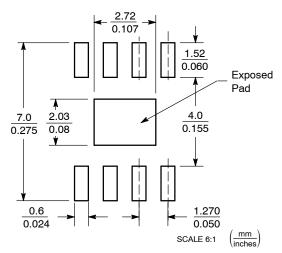
#### **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
  2. DIMENSIONS IN MILLIMETERS (ANGLES
- 2. DIMENSIONS IN MILLIMETERS (ANGLE: IN DEGREES).
  3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 MM TOTAL IN EXCESS OF THE "b" DMENSION OF THE "b" DMENSION AT HAVE AND ANTERIAL. DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 4. DATUMS A AND B TO BE DETERMINED AT DATUM PLANE H.

	MILLIMETERS				
DIM	MIN	MAX			
Α	1.35	1.75			
A1	0.00	0.10			
A2	1.35	1.65			
b	0.31	0.51			
b1	0.28	0.48			
С	0.17	0.25			
с1	0.17 0.23				
D	4.90	BSC			
E	6.00	BSC			
E1	3.90	BSC			
е	1.27	BSC			
L	0.40	1.27			
L1	1.04	REF			
F	2.24	3.20			
G	1.55	2.51			
h	0.25	0.50			
θ	0° 8°				

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

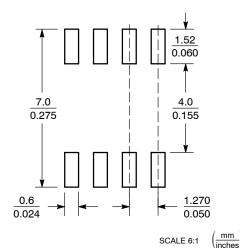
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#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A AND B DO NOT INCLUDE
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR
- 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMILM MATERIAL CONDITION.
- MAXIMUM MATERIAL CONDITION.
  6. 751–01 THRU 751–06 ARE OBSOLETE. NEW STANDARD IS 751–07.

	MILLIN	IETERS	INC	HES		
DIM	MIN MAX		MIN	MAX		
Α	4.80	5.00	0.189	0.197		
В	3.80	4.00	0.150	0.157		
C	1.35	1.75	0.053	0.069		
D	0.33	0.51	0.013	0.020		
G	1.27	1.27 BSC		0 BSC		
Н	0.10	0.25	0.004	0.010		
J	0.19	0.25	0.007	0.010		
K	0.40	1.27	0.016	0.050		
М	0 °	8 °	0 °	8 °		
N	0.25	0.50	0.010	0.020		
S	5.80	6.20	0.228	0.244		

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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